

# AT54HCxxx

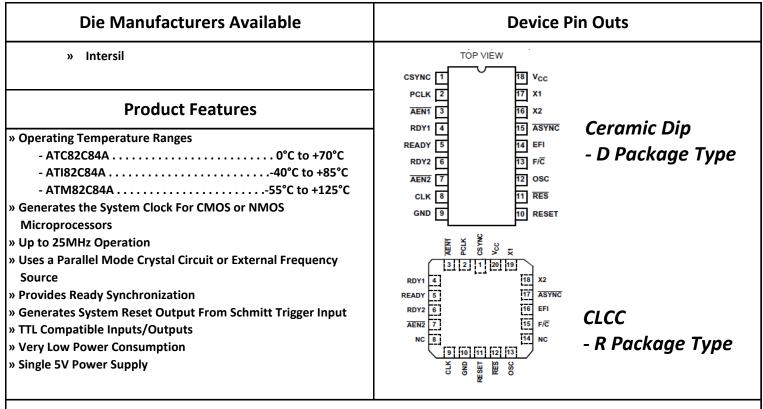
#### **Device Offerings**

Anloy Technologies is offering packaging of original manufacturers die in many of today's obsolete packages. Below is a list of the 54HC series die that is at the time of drafting this document in Anloy Technologies inventory in production level quantities immediately available for manufacture. Many of these part number dies are available from multiple original manufacturers such as Texas Instruments, National Semiconductor, Motorola, Fairchild Semiconductor, and many others. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.

54HC00	54HC113	54HC191	54HC365	54HC4049
54HC02	54HC125	54HC193	54HC367	54HC4052
54HC03	54HC126	54HC194	54HC373	54HC4060
54HC04	54HC132	54HC195	54HC374	54HC4066
54HC05	54HC133	54HC237	54HC386	54HC4075
54HC08	54HC137	54HC238	54HC393	54HC4078
54HC10	54HC138	54HC240	54HC407	54HC4514
54HC11	54HC139	54HC241	54HC534	54HC4520
54HC14	54HC148	54HC242	54HC540	54HC40103
54HC20	54HC151	54HC243	54HC541	
54HC21	54HC154	54HC244	54HC573	
54HC27	54HC157	54HC251	54HC574	
54HC30	54HC158	54HC253	54HC590	
54HC32	54HC160	54HC257	54HC645	
54HC42	54HC161	54HC258	54HC684	
54HC74	54HC163	54HC259	54HC688	
54HC75	54HC164	54HC266	54HC804	
54HC85	54HC165	54HC273	54HC4002	
54HC86	54HC166	54HC280	54HC4009	
54HC97	54HC173	54HC283	54HC4017	
54HC107	54HC174	54HC288	54HC4020	
54HC109	54HC175	54HC299	54HC4024	
54HC112	54HC190	54HC356	54HC4040	



## 82C84A

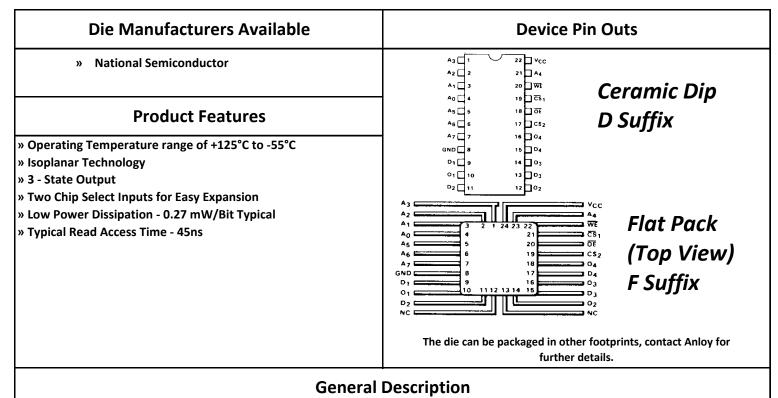


#### **General Description**

The Anloy 82C84A is a high performance CMOS Clock Generator-driver which is designed to service the requirements of both CMOS and NMOS microprocessors such as the 80C86, 80C88, 8086 and the 8088. The chip contains a crystal controlled oscillator, a divide-by-three counter and complete "Ready" synchronization and reset logic. Static CMOS circuit design permits operation with an external frequency source from DC to 25MHz. Crystal controlled operation to 25MHz is guaranteed with the use of a parallel, fundamental mode crystal and two small load capacitors. All inputs (except X1 and RES) are TTL compatible over temperature and voltage ranges. Power consumption is a fraction of that of the equivalent bipolar circuits. This speed-power characteristic of CMOS permits the designer to custom tailor his system design with respect to power and/or speed requirements. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



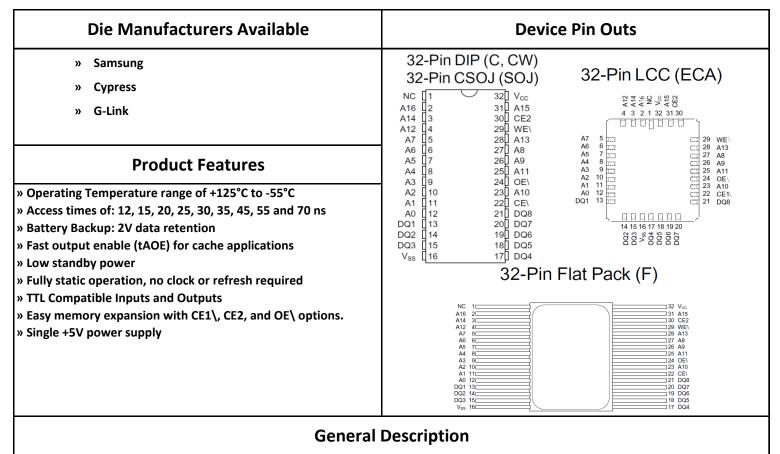
# AT93L422



The 93L422 is a 1024-bit Read/Write Random Access Memory organized as 256 words by four bits per word. The 93L422 has 3-state outputs, and is designed primarily for buffer control storage and high performance main memory applications. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



# AT5C1008

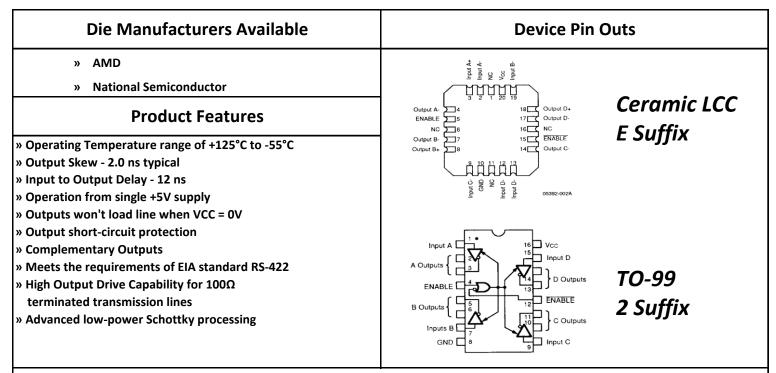


The AT5C1008 SRAM employs high-speed, low power CMOS designs using a four-transistor memory cell, and are fabricated using double-layer metal, double-layer polysilicon technology. For design flexibility in high-speed memory applications, this device offers dual chip enables (CE1\, CE2) and output enable (OE\). These control pins can place the outputs in High-Z for additional flexibility in system design. All devices operate from a single +5V power supply and all inputs and outputs are fully TTL compatible. Writing to these devices is accomplished when write enable (WE\) and CE1\ inputs are both LOW and CE2 is HIGH. Reading is accomplished when WE\ and CE2 remain HIGH and CE1\ and OE\ go LOW. The devices offer a reduced power standby mode when disabled, allowing system designs to achieve low standby power requirements. The "L" version offers a 2V data retention mode, reducing current consumption to 1mA maximum. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



Quad High Speed Differential Line Driver

## AT26LS31



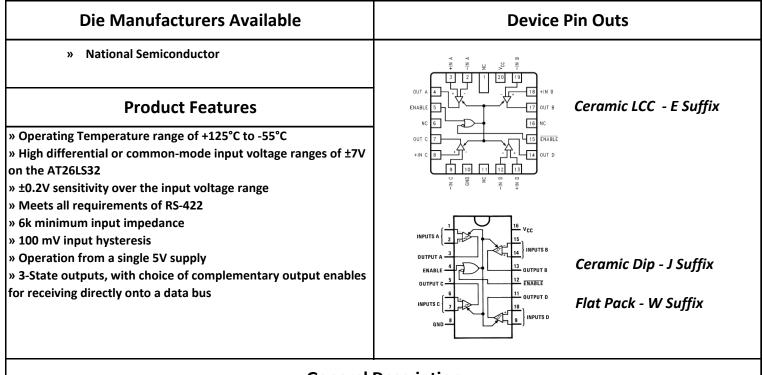
#### **General Description**

The AT26LS31 is a quad-differential line driver, designed for digital data transmission over balanced lines. The AT26LS31 meets all the requirements of EIA standard RS422. It is designed to provide unipolar differential drive to twisted pair or parallel wire transmission lines. The circuit provides an enable and disable function common to all four drivers. The AT26LS31 features 3-state output and logical OR-ed complementary enable inputs. The inputs are all LS compatible and are one unit load. The AT26LS31 is constructed using advanced low power Schottky processing. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



Quad High Speed Differential Line Reciver

# AT26LS32



#### **General Description**

The AT26LS32 is a quad differential line receivers designed to meet the RS-422 requirements for balanced and unbalanced digital data transmission. The AT26LS32 has an input sensitivity of 200 mV over the input voltage range of ±7V. The AT26LS32 has an enable and disable function common to all four receivers and features 3-state outputs with 8 mA sink capability. Constructed using low power Schottky processing, these devices are available over the full military and commerical operating temperature ranges. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



# ATM27C64

Die Manufacturers Available	Device Pin Outs
» Fujitsu	
Product Features	A12 2 27 PGN Windowed A7 3 26 NC A6 4 25 A8 Ceramic Dip
<ul> <li>» Operating Temperature range of +125°C to -55°C</li> <li>» CMOS power consumption : 550 μW max. Standby 165mW max. Active</li> <li>» 8,192 words by 8 bits organization, fully decoded</li> <li>» Programs with one 50ms or 1ms pulse</li> <li>» No clock required (fully static operation)</li> <li>» TTL compatible inputs and outputs</li> <li>» Output enable pin for simplified memory expansion</li> <li>» Fast access times available: 200ns, 150ns, or 300ns</li> <li>» Single +5V operation</li> </ul>	A5 A5 A5 A5 A5 A5 A5 A5

#### **General Description**

The ATM27C64 is a high speed 65,536-bit static complementary MOS erasable and electrically reprogrammable read only memory (EPROM) it is especially well suited for applications where rapid turn around and or bit pattern experimentation and low power consumption are important. The windowed lid allows the user to expose the device to ultra-violet light in order to erase the memory bit pattern previously programmed. At the completion of erasure, a new pattern can then be written to memory. The ATM27C64 is fabricated using CMOS double polysilicon gate technology with single transistor stacked gate cells. It is organized as 8,192 words by 8 bits for use in microprocessor applications. Single +5V operation greatly facilitates its use in systems. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



32K x 8 Static RAM

# AT5C2568

Die Manufacturers Available	Device Pi	n Outs
» Samsung	28-PIN SOJ (DCJ) 28-Pin DIP (C, CW)	32-Pin LCC (ECW)
» Cypress	A14 [1 28] V <sub>CC</sub> A12 [2 27] WE\ A7 [3 26] A13 A6 [4 25] A8	4 3 2 1 32 31 30
Product Features	A5 []5 24] A9 A4 []6 23] A11 A3 []7 22] OE\ A2 []8 21] A10	A6         5         29         A8           A5         6         28         A9           A4         7         27         A11           A3         8         26         NC           A2         9         25         OE           A1         10         24         A10
» Operating Temperature range of +125°C to -55°C	A1 09 200 CE	A0 11 23 CE\ NC 12 22 DQ8
» Access Times: 12, 15, 20, 25, 35, 45, 55, 70, & 100ns	DQ1 [11 18] DQ7	
» Battery Backup: 2V data retention	DQ2 [12 17] DQ6 DQ3 [13 16] DQ5	14 15 16 17 18 19 20 S S S S S S S S S S S S S S S S S S S
» Low power standby	V <sub>SS</sub> [14 15] DQ4	
» High-performance, low-power CMOS double-metal process		28-Pin LCC (EC)
» Single +5V (+10%) Power Supply	28-Pin Flat Pack (F)	3 2 1 28 27 M 21 21 21 M 21 21 21
» Easy memory expansion with CE\		
» All inputs and outputs are TTL compatible	A14       1         A12       2         A7       3         A6       4         A5       5         A4       6         A3       7         A2       8         A1       9         DQ1       11         DQ2       12         DQ3       13         V <sub>85</sub> 14	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$
General	Description	

#### General Description

The Anloy AT5C2568 SRAM employs high-speed, low power CMOS designs using a four-transistor memory cell, and are fabricated using double-layer metal, double-layer polysilicon technology.For flexibility in high-speed memory applications, Anloy offers chip enable (CE\) and output enable (OE\) capability. These enhancements can place the outputs in High-Z for additional flexibility in system design. Writing to these devices is accomplished when write enable (WE\) and CE\ inputs are both LOW. Reading is accomplished when WE\ remains HIGH and CE\ and OE\ go LOW. The device offers a reduced power standby mode when disabled. This allows system designs to achieve low standby power requirements. The "L" version provides a battery backup/low voltage data retention mode, offering 2mW maximum power dissipation at 2 volts. All devices operate from a single +5V power supply and all inputs and outputs are fully TTL compatible. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



## AT5C4008

Die Manufacturers Available	Device Pin Outs
<ul> <li>» Samsung</li> <li>» Cypress</li> </ul> Product Features » Operating Temperature range of +125°C to -55°C » High Speed: 15, 17, 20, 25, 35 and 45ns » High-performance, low power military grade device » Single +5V ±10% power supply » Easy memory expansion with CE\ and OE\ options » All inputs and outputs are TTL-compatible » Ease of upgradability from 1 Meg using the 32 pin evolutionary version.	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

#### **General Description**

The AT5C4008 is a 4 megabit monolithic CMOS SRAM, organized as a 512K x 8. The evolutionary 32 pin device allows for easy upgrades from the 1 meg SRAM. For flexibility in high-speed memory applications, Anloy device offers chip enable (CE\) and output enable (OE\) capabilities. These enhancements can place the outputs in High-Z for additional flexibility in system design. Writing to these devices is accomplished when write enable (WE\) and CE\ inputs are both LOW. Reading is accomplished when WE\ remains HIGH and CE\ and OE\ go LOW. This allows systems designers to meet low standby power requirements. All devices operate from a single +5V power supply and all inputs are fully TTL-Compatible. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



High Speed 12-Bit A/D Converter with External Reference Input

# AT912AXS

## **General Description**

The **AT912AXS** is a custom replacement device manufactured by Anloy Technologies designed to be a near identical solution for the obsolete ADC912A in applications where the HBEN function of the ADC912 is not required. The AT912AXS is also custom manufactured to exceed the original ADC912A temperature range of -40°C to +85°C and instead is rated for -55°C to +125°C while still maintaining a footprint compatible with the ADC912AFS layout. The Analog input range is pre selected for 0 to +10V operation, other operation ranges are available.

AIN	1 -		- 24	VDD
VREFIN	2 -		- 23	VSS
AGND	3 -		- 22	/BUSY
D11	4 -		- 21	/CS
D10	5 -		- 20	/RD
D9	6 -	TOP	- 19	NC
D8	7 -	VIEW	- 18	CLKOUT
D7	8 -		- 17	CLKIN
D6	9 -		- 16	D0
D5	10 -		- 15	D1
D4	11 -		- 14	D2
DGND	12 -		- 13	D3

#### 24 Lead Wide Body Ceramic SOIC

		·			
DD = +5V ± 5%, VSS = -11.4C to -15.75C, V	REFIN = -5V, Analog inp	out 0V to 10V, External FCLK = 1.25MHz, noted.	Temp Range of -5	5°C to +125°C ו	unless otherw
Parameter	Symbol	Conditions	Min	Max	Unit
		Static Accuracy	÷	· · · · ·	
Integral Nonlinearity	INL		-1	+1	LSB
Differential Nonlinearity	DNL		-1	+1	LSB
Offset Error	VZSE	VDD=+5V, VSS=-12V	-5	+5	LSB
Gain Error	GFSE	VDD=+5V, VSS=-12V	-6	+6	LSB
		Analog Input			
Input Voltage Range	VIN		0	10	V
Input Current Range	IIN		0	3	mA
		Power Supplies			
Positive Supply Current	IDD	VDD=+5V		7	mA
Negative Supply Current	ISS	VSS=-12V		10	mA
Power Consumption	PDISS	VDD=+5V, VSS=-12V		155	mW
Power Supply Rejection Ratio	PSRR+	ΔVDD=±5%, AIN=10V		4	LSB
	PSRR-	ΔVDD=±5%, AIN=10V		4	LSB

# AT912AXS

		Digital Inputs			
Logic Input High Voltage	VINH		2.4		V
Logic Input Low Voltage	VINL			0.8	V
Logic Input Current	IIN	/CS, RD; VIN = 0 to VDD		±10	μA
		CLKIN; VIN = 0 to VDD		±20	μΑ
Digital Input Capacitance	CIN			10	pF
		Digital Outputs			
Logic Output High Voltage	VOH	/CS, /RD	4		V
Logic Output Low Voltage	VOL	/CS, /RD		0.4	V
Three-State Output Leakage	IOZ	/CS, /RD		10	μA
Digital Output Capacitance	COUT	Digital Inputs, /CS, /RD, CLKIN		15	pF
		Dynamic Performance			
Conversion Time	тс	fCLK = 1.25 MHz			
		Synchronous Clock		10.4	μs
		Asynchronous Clock	10.4	11.2	μs
/CS to /RD Setup Time	t1	(Note 3)	0		ns
/RD to /BUSY Propagation Delay	t2	CL = 50 pF		150	ns
Data Access Time After READ	t3	CL = 100 pF (Note 3)		125	ns
Read Pulse width	t4	(Note 3)	90		ns
/CS to /RD Hold Time	t5	(Note 3)	0		ns
Data Setup after /BUSY	t6	CL = 100 pF		90	ns
Delay between Successive Reads	t10	(Note 3)	350		ns

Note 1: Performance guaranteed over supply range by testing end point errors (power-supply rejection) and the supply extremes

Note 2: VDD=+5V, VSS=-12V, VREF=-5V

Note 3: Guaranteed by Design

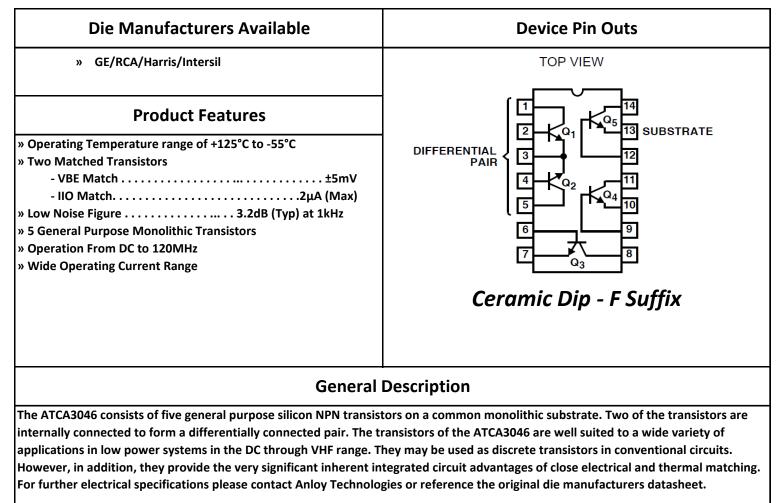
Note 4: All inputs are 0V to +5V swing with tr = tf = 5ns (10% to 90% of +5V) and timed from a voltage level of +1.6V

Absolute Maximum Ratings				
VDD to DGND	-0.3V to +7V			
VSS to DGND	+0.3V to -7V			
VREFIN to DGND	VSS to VDD			
AGND to DGND	-0.3V to VDD +0.3V			
AIN to AGND	-15V to +15V			
Digital Input Voltage to DGND	-0.3V to VDD +0.3V			
Digital Output Voltage to DGND	-0.3V to VDD +0.3V			
Operational Temperature Range	-55°C to +125°C			

#### 1924 American Dr, Lago Vista TX 78645 Ph (512) 388-2313 Fax (512) 388-2781



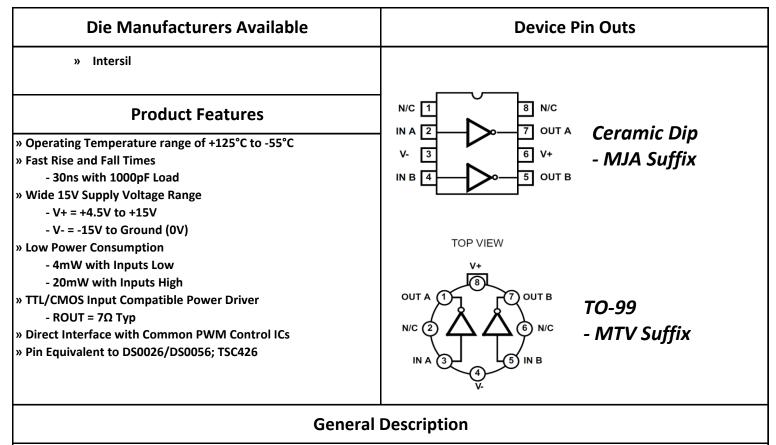
# ATCA3046





**Dual Power MOSFET Driver** 

# ATICL7667



The ATICL7667 is a dual monolithic high-speed driver designed to convert TTL level signals into high current outputs at voltages up to 15V. Its high speed and current output enable it to drive large capacitive loads with high slew rates and low propagation delays. With an output voltage swing only millivolts less than the supply voltage and a maximum supply voltage of 15V, the ATICL7667 is well suited for driving power MOSFETs in high frequency switched-mode power converters. The ATICL7667's high current outputs minimize power losses in the power MOSFETs by rapidly charging floand discharging the gate capacitance. The ATICL7667's inputs are TTL compatible and can be directly driven by common pulse-width modulation control ICs. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



# ATICM7555M

Die Manufacturers Available	Device Pin	Outs
» Harris/Intersil		
Product Features	TRIGGER 2 7 DISCHARGE OUTPUT 3 6 THRESHOLD	Ceramic Dip JD Suffix
<ul> <li>» Operating Temperature range of +125°C to -55°C</li> <li>» Exact Equivalent in Most Cases for SE/NE555 or TLC555</li> </ul>	RESET 4 5 CONTROL VOLTAGE	JU JUJJIN
<ul> <li>» Low Supply Current</li></ul>	V <sub>DD</sub> AND CASE	TO-99
» Temperature Stability 0.005%/°C at 25°C » Can be Used with Higher Impedance Timing Elements		TV Suffix
than Regular 555 for Longer RC Time Constants » Timing from Microseconds through Hours		
<ul> <li>» Operates in Both Astable and Monostable Modes</li> <li>» High Output Source/Sink Driver can Drive TTL/CMOS</li> <li>» Outputs have Very Low Offsets, HI and LO</li> </ul>		

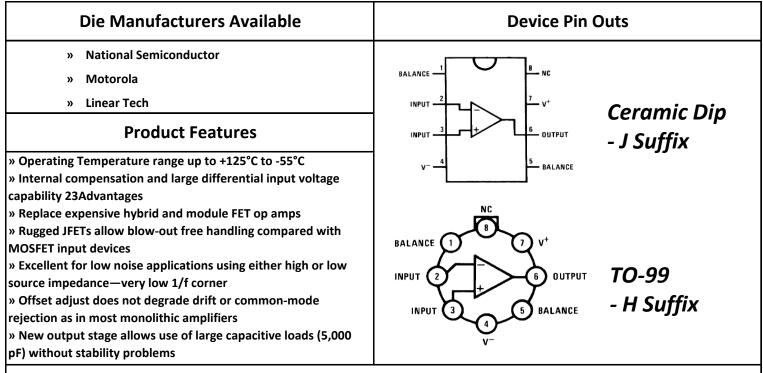
#### **General Description**

The ICM7555 is a CMOS RC timer providing significantly improved performance over the standard SE/NE555 and 355 timers, while at the same time being a direct replacement in most applications. Improved parameters include low supply current, wide operating supply voltage range, low THRESHOLD, TRIGGER and RESET currents, no crow barring of the supply current during output transitions, higher frequency performance and no requirement to decouple CONTROL VOLTAGE for stable operation. Specifically, the ICM7555 is a stable controller capable of producing accurate time delays or frequencies. In the one shot mode, the pulse width of each circuit is precisely controlled by one external resistor and capacitor. For astable operation as an oscillator, the free running frequency and the duty cycle are both accurately controlled by two external resistors and one capacitor. Unlike the regular bipolar 555 devices, the CONTROL VOLTAGE terminal need not be decoupled with a capacitor. The circuits are triggered and reset on falling (negative) waveforms, and the output inverter can source or sink currents large enough to drive TTL loads, or provide minimal offsets to drive CMOS loads. For further electrical specifications please reference the original die manufacturers datasheet.



#### JFET Input Operational Amplifiers

LF155, LF156, LF157, LF355, LF356, LF357



#### **General Description**

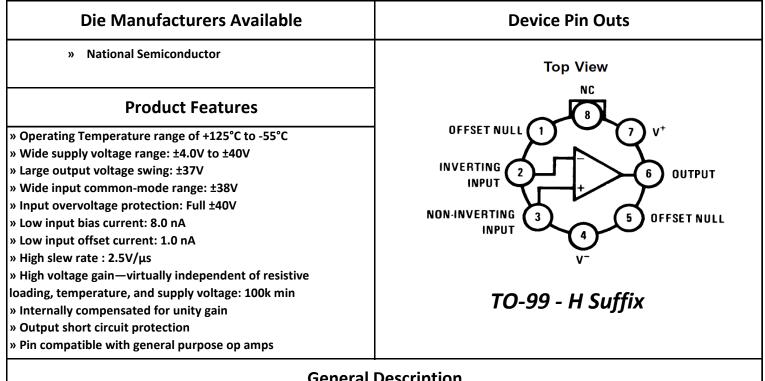
These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors. These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.

	Additional Information				
	LF155 LF156 LF157 LF355 LF356 LF357 (Av=5) Units				
xteremely fast settling time to 0.01%	4	1.5	1.5	μs	
Fast slew rate	5	12	50	V/µs	
Wide gain bandwidth	2.5	5	20	MHz	
Low input noise voltage	20	12	12	nV / √Hz	



High Voltage **Operational Amplifier** 

# ATLM143/ATLM343

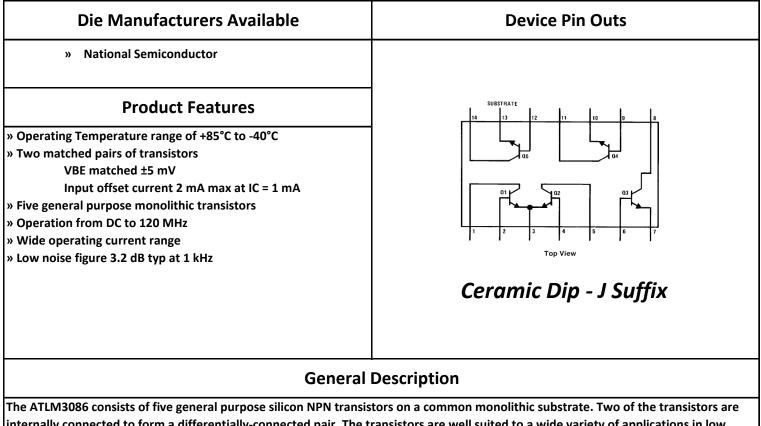


#### **General Description**

The ATLM143 is a general purpose high voltage operational amplifier featuring operation to ±40V, complete input overvoltage protection up to ±40V and input currents comparable to those of other super-b op amps. Increased slew rate, together with higher common-mode and supply rejection, insure improved performance at high supply voltages. Operating characteristics, in particular supply current, slew rate and gain, are virtually independent of supply voltage and temperature. Furthermore, gain is unaffected by output loading at high supply voltages due to thermal symmetry on the die. The ATLM143 is pin compatible with general purpose op amps and has offset null capability. Application areas include those of general purpose op amps, but can be extended to higher voltages and higher output power when externally boosted. For example, when used in audio power applications, the ATLM143 provides a power bandwidth that covers the entire audio spectrum. In addition, the ATLM143 can be reliably operated in environments with large overvoltage spikes on the power supplies, where other internally-compensated op amps would suffer catastrophic failure. The ATLM343 is similar to the ATLM143 for applications in less severe supply voltage and temperature environments. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



# ATLM3086



internally connected to form a differentially-connected pair. The transistors are well suited to a wide variety of applications in low power system in the DC through VHF range. They may be used as discrete transistors in conventional circuits however, in addition, they provide the very significant inherent integrated circuit advantages of close electrical and thermal matching. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



#### Micropower Voltage Reference

LM185-1.2/LM285-1.2/ LM385-1.2

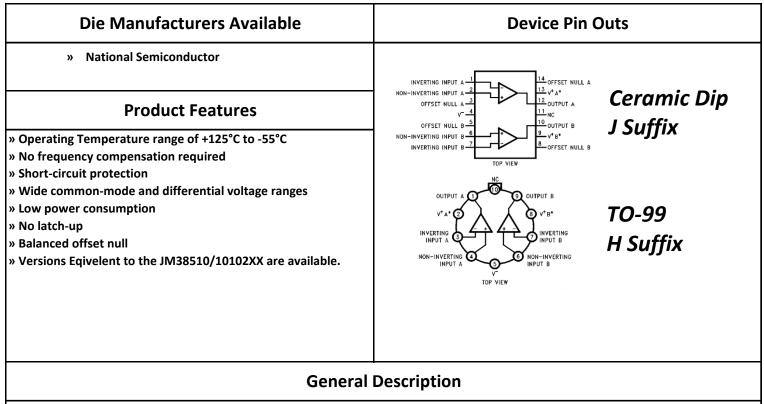
Die Manufacturers Available	Device Pin Outs
<ul> <li>» Linear Tech</li> <li>» Motorola</li> <li>» National Semiconductor</li> </ul>	BOTTOM VIEW
Product Features » 10mA to 20mA Operating Range » Guaranteed 1% Initial Voltage Tolerance » Guaranteed 1W Dynamic Impedance » Very Low Power Consumption	H PACKAGE 2-LEAD TO-46 METAL CAN
Genera	Description
The ATLM185-1.2 is a two terminal band gap reference diode tha	t has been designed for applications which require precision

The ATLM185-1.2 is a two terminal band gap reference diode that has been designed for applications which require precision performance with micropower operation. The device provides guaranteed operating specifications at currents as low as 10mA. The nominal voltage is 1.235V with both 1% and 2% tolerances available. Some additional features are: maximum dynamic impedance of 1W, low noise and excellent stability over time and temperature. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



#### **Dual Operational Amplifier**

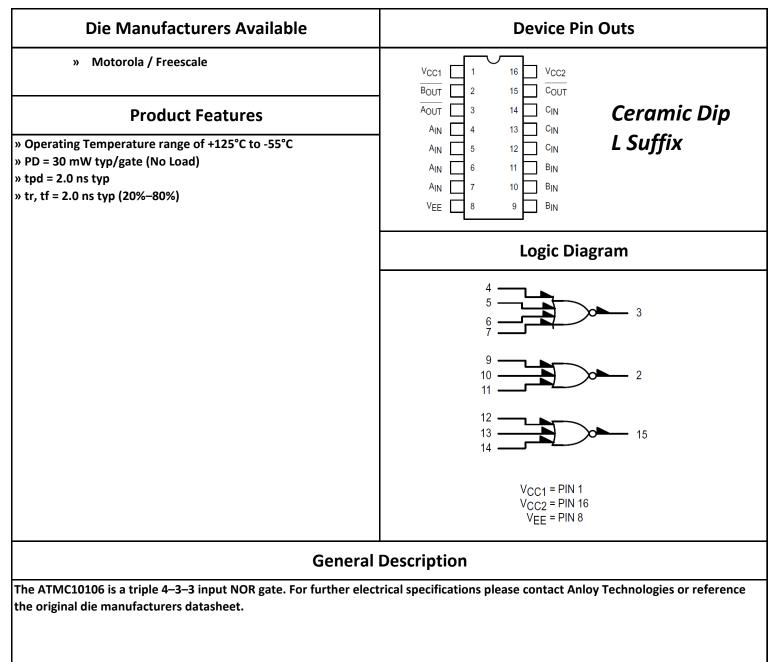
## LM747A



The LM747A is a general purpose dual operational amplifier. The two amplifiers share a common bias network and power supply leads. Otherwise, their operation is completely independent. Additional features of the LM747A are: no latch-up when input common mode range is exceeded, freedom from oscillations, and package flexibility. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



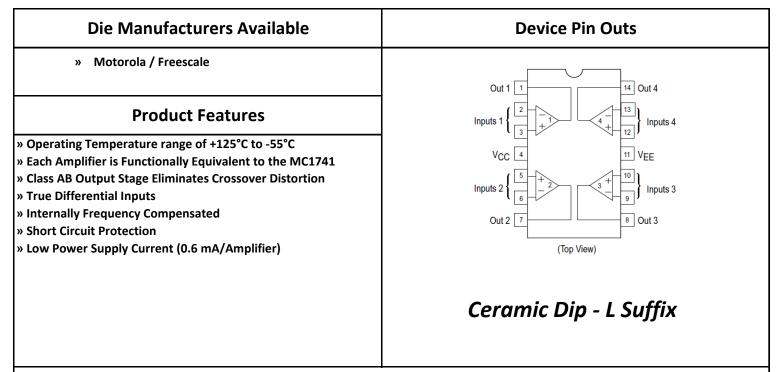
# ATMC10106





#### Quad Differential Input Operational Amplifier





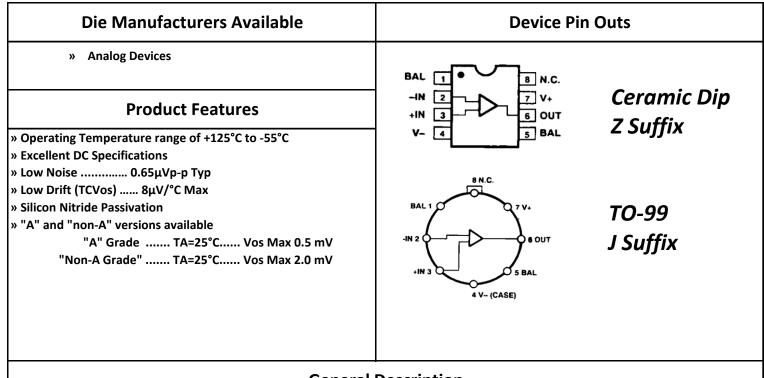
#### **General Description**

The ATMC4741C is a true quad MC1741. Integrated on a single monolithic chip are four independent, low power operational amplifiers which have been designed to provide operating characteristics identical to those of the industry standard MC1741, and can be applied with no change in circuit performance. The ATMC4741C can be used in applications where amplifier matching or high packing density is important. Other applications include high impedance buffer amplifiers and active filter amplifiers. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



#### General Purpose Operational Amplifier

## ATOP02



#### **General Description**

The OP02 is a high performance general purpose operational amplifier that provides significant improvements over industry-standard and premium 741 types while maintaining pin-for-pin compatibility and ease of application. Key specifications such as Vos, Ios, IB, CMRR, PSRR, and Avo are guaranteed over the full operating temperature range. A thermally symmetrical input-stage design provides low input offset voltage drift and insensitivity to output load conditions. The OP-02 is a direct replacement for the 741. It is ideal for upgrading existing designs where accuracy improvements at required and for elimination special low-drift or low-noise selected types. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



+2.5V Low Power Precision Voltage Reference

# ATREF43

Die Manufacturers Available	Device Pin Outs	
» Analog Devices	ېن د ۲۰۰۰	
Product Features	$- \underbrace{\begin{array}{c} z \in z \in z \\ \exists z \mid 1 2019 \\ v_{iN} \end{bmatrix}}_{i \in IT} \underbrace{\begin{array}{c} Ceramic LCO \\ BRC Suffix \\ v_{iN} \end{bmatrix}}_{i \in IT}$	C
» Operating Temperature range of +125°C to -55°C	N.C. 6 16 N.C.	
» +2.5 Volt Output: ±0.05% Max	TEMP 7 15 V <sub>OUT</sub> N.C. 8 14 N.C.	
» Low Temperature Coefficient: 10 ppm/°C Max		
<ul> <li>» Excellent Regulation</li> <li>» Load Regulation: 20 ppm/mA Max</li> </ul>	S ND	
» Line Regulation: 20 ppm/V Max	TEST*	
» Supply Current: 450µA Max	8	
» Temperature Voltage Output: +1.9mV/°C	TEST* 1 N.C.	
» Operating Voltage Range: +4.5V to +40V	$V_{\rm IN} = \left( \begin{array}{c} V_{\rm O} \\ \end{array} \right)_6 V_{\rm OUT}  TO-99$	
» Wide Common-Mode Voltage		
» Range, V– to within 1.5 V of V+		
» Pin Compatible with 1458, LM158, LM2904	4 GROUND (CASE)	

#### **General Description**

The REF43 is a low power precision reference providing a stable 2.5 V output independent of variations in supply voltage, load conditions or ambient temperature. It is suitable as a reference level for 8-, 10- and 12-bit data acquisition systems, or wherever a stable, known voltage is required. Tight output tolerances and low thermal drift are assured by zener-zap trimming of both output voltage and its temperature coefficient. A unique curvature correction circuit reduces the thermal curvature which is characteristic of many previous bandgap references. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.



N-Channel Enhancement-Mode Vertical DMOS FET

# ATVN0109

Die Manufacturers Available	Device Pin Or	Device Pin Outs	
» Supertex			
Product Features			
» Basic Electrical Charecteristics			
BVDSS/BVDGS 90 V			
RDS(ON) 3.0Ω max			
ID(ON) 2.0A min		TO-52	
» Operating Temperature range of +125°C to -55°C		N9 Suffix	
» Free from secondary breakdown	ູ່		
» Low power drive requirement	DGS		
» Ease of paralleling			
» Low CISS and fast switching speeds			
» Excellent thermal stability	Case: DRAIN		
» Integral source-drain diode	Case. DIVAIN		
» High input impedance and high gain			
Gener	al Description		

These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure. This produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown. These vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired. For further electrical specifications please contact Anloy Technologies or reference the original die manufacturers datasheet.